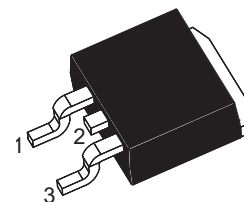
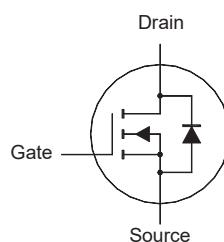


N-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Surface-mounted package
- Low Gate-Source Threshold Voltage
- Halogen and Antimony Free(HAF), RoHS compliant



1.Gate 2.Drain 3.Source
TO-263 Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DSS}	40	V
$R_{DS(ON)}$ Max	4 @ $V_{GS} = 10\text{ V}$	$m\Omega$
	5 @ $V_{GS} = 4.5\text{ V}$	
$V_{GS(th)}$ typ	1.5	V
Q_g typ	143 @ $V_{GS} = 10\text{ V}$	nC

Absolute Maximum Ratings(at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	105	A
		73	
Peak Drain Current, Pulsed ¹⁾	I_{DM}	500	A
Avalanche Current	I_{AS}	58.8	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	172.8	mJ
Power Dissipation	P_D	83.3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	30	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 175^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 58.8\text{ A}$, $V_{GS} = 10\text{ V}$.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at T_a = 25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at I _D = 250 μ A	BV _{DSS}	40	-	-	V
Drain-Source Leakage Current at V _{DS} = 32 V	I _{DSS}	-	-	1	μ A
Gate Leakage Current at V _{GS} = $\pm$ 16 V	I _{GSS}	-	-	$\pm$ 100	nA
Gate-Source Threshold Voltage at V _{DS} = V _{GS} , I _D = 250 μ A	V _{GS(th)}	1	-	2.5	V
Drain-Source On-State Resistance at V _{GS} = 10 V, I _D = 30 A at V _{GS} = 4.5 V, I _D = 20 A	R _{DS(on)}	- -	3.4 -	4 5	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at V _{DS} = 5 V, I _D = 20 A	g _{fs}	-	55.8	-	S
Gate Resistance at V _{GS} = 0 V, V _{DS} = 0 V, f = 1 MHz	R _g	-	0.5	-	Ω
Input Capacitance at V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz	C _{iss}	-	7007	-	pF
Output Capacitance at V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz	C _{oss}	-	549	-	pF
Reverse Transfer Capacitance at V _{GS} = 0 V, V _{DS} = 20 V, f = 1 MHz	C _{rss}	-	404	-	pF
Gate charge total at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A at V _{DS} = 20 V, V _{GS} = 4.5 V, I _D = 30 A	Q _g	- -	143 68	- -	nC
Gate to Source Charge at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A	Q _{gs}	-	22	-	nC
Gate to Drain Charge at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A	Q _{gd}	-	28	-	nC
Turn-On Delay Time at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A, R _g = 3.3 Ω	t _{d(on)}	-	40	-	ns
Turn-On Rise Time at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A, R _g = 3.3 Ω	t _r	-	63	-	ns
Turn-Off Delay Time at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A, R _g = 3.3 Ω	t _{d(off)}	-	37	-	ns
Turn-Off Fall Time at V _{DS} = 20 V, V _{GS} = 10 V, I _D = 30 A, R _g = 3.3 Ω	t _f	-	9	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at I _S = 1 A, V _{GS} = 0 V	V _{SD}	-	-	1.2	V
Body-Diode Continuous Current	I _S	-	-	105	A
Body-Diode Continuous Current, Pulsed	I _{SM}	-	-	500	A
Body Diode Reverse Recovery Time at I _S = 30 A, di/dt = 100 A / μ s	t _{rr}	-	21	-	ns
Body Diode Reverse Recovery Charge at I _S = 30 A, di/dt = 100 A / μ s	Q _{rr}	-	13	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

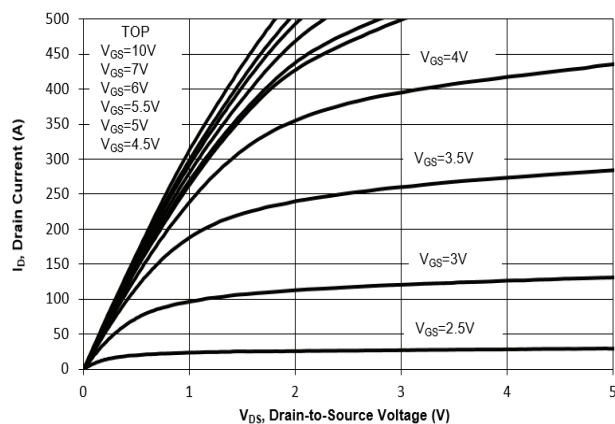


Fig. 2 Typical Transfer Characteristics

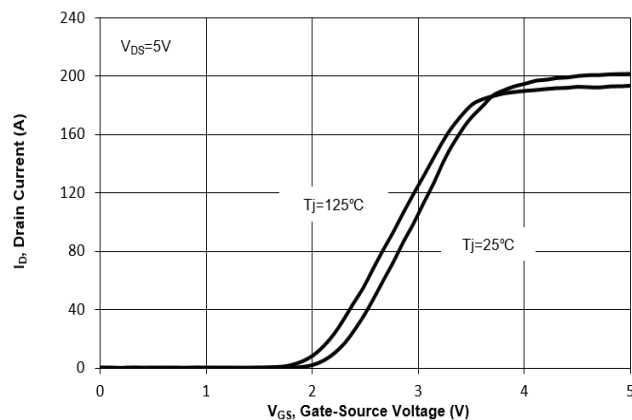


Fig. 3 On-Resistance vs. Drain Current

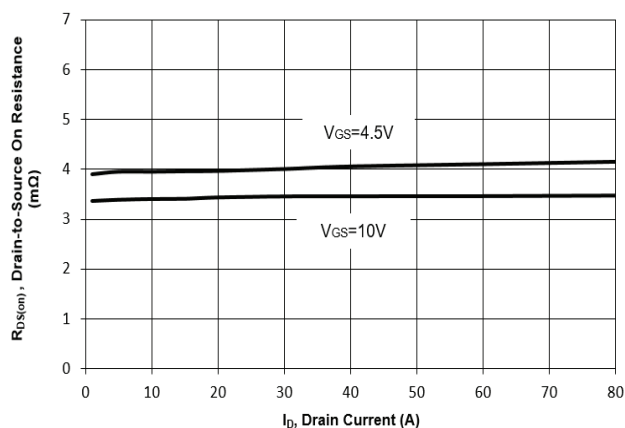


Fig. 4 On-Resistance vs. Gate to Source Voltage

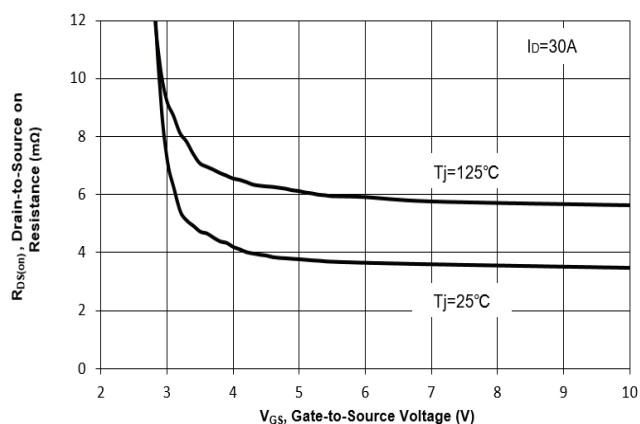


Fig. 5 On-Resistance vs. Tj

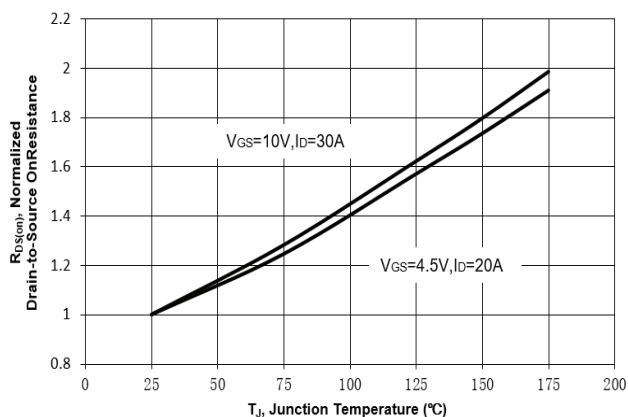
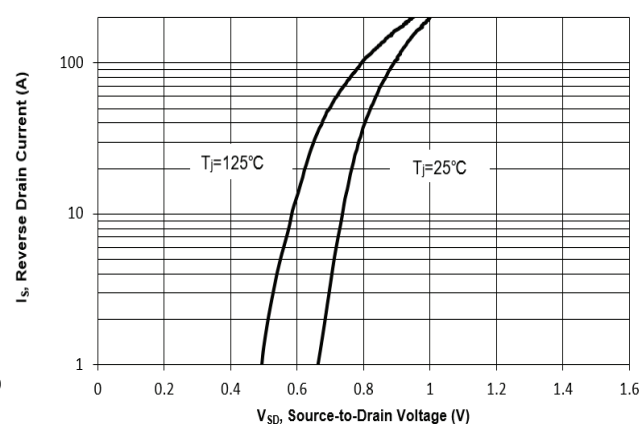


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

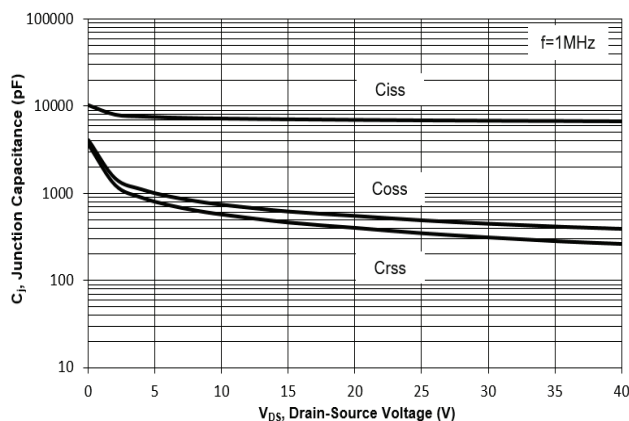


Fig. 8 Drain-Source Leakage Current vs. T_j

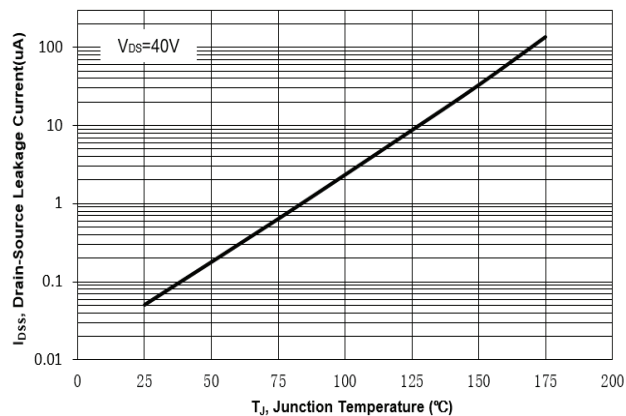


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

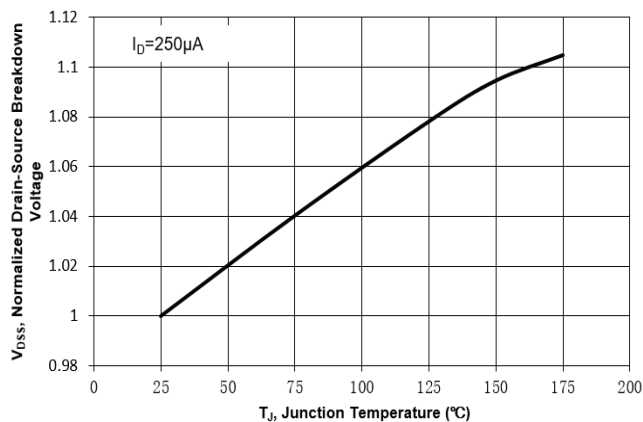


Fig. 10 Gate Threshold Variation vs. T_j

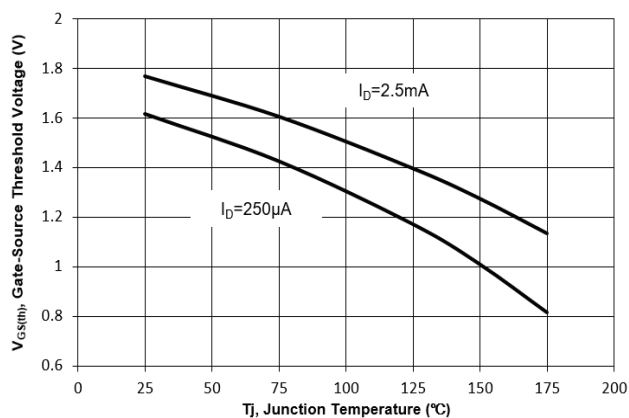


Fig. 11 Gate Charge

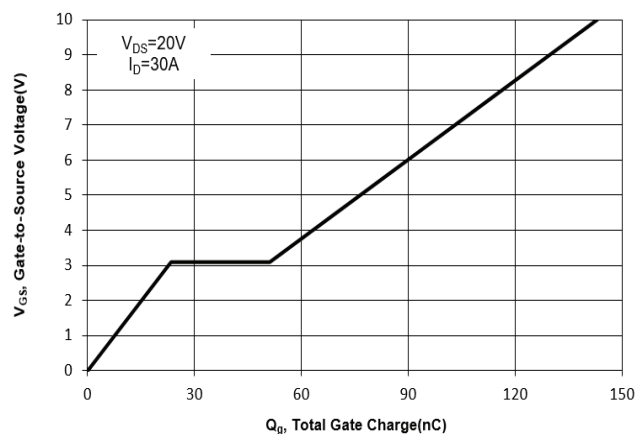
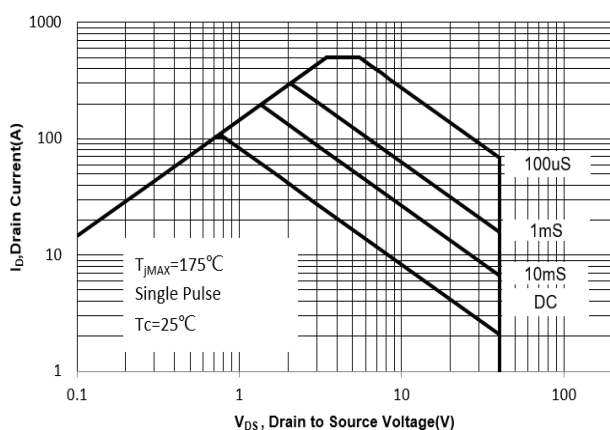


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

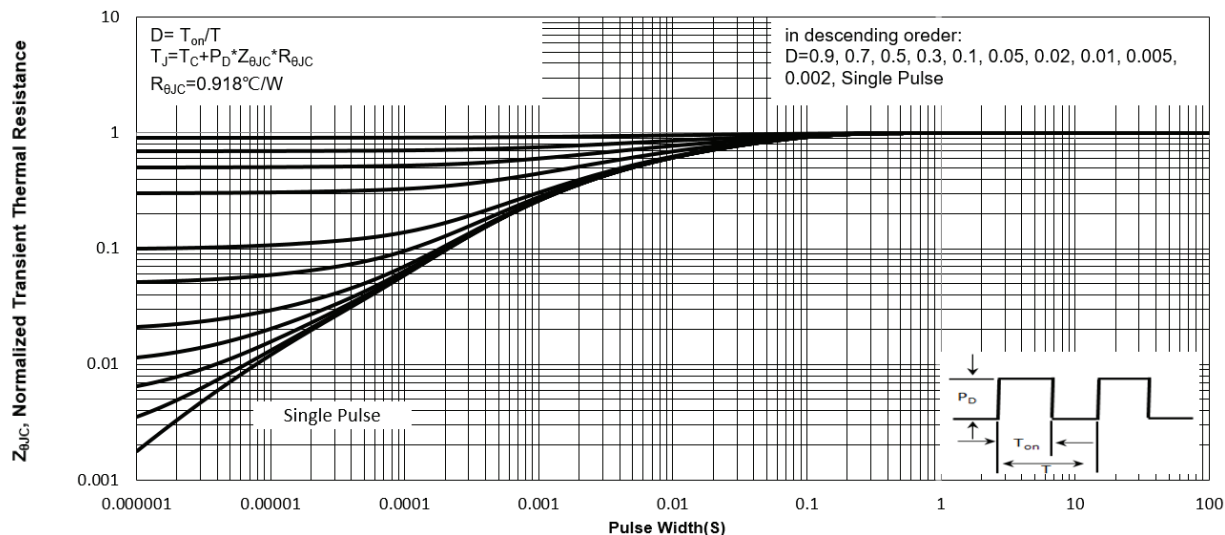
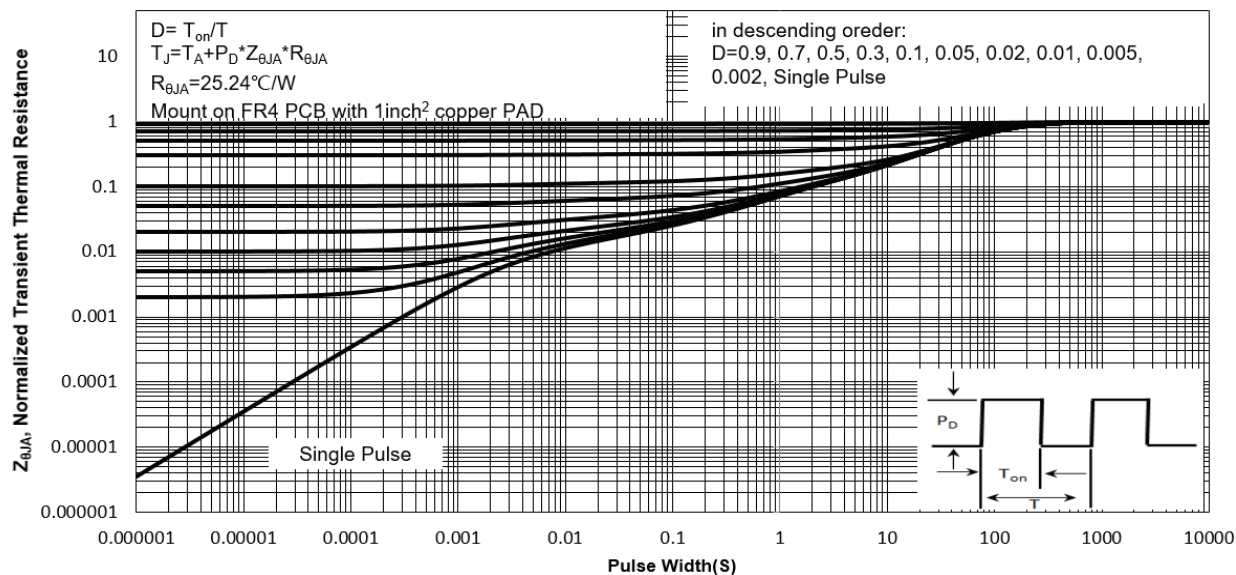


Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

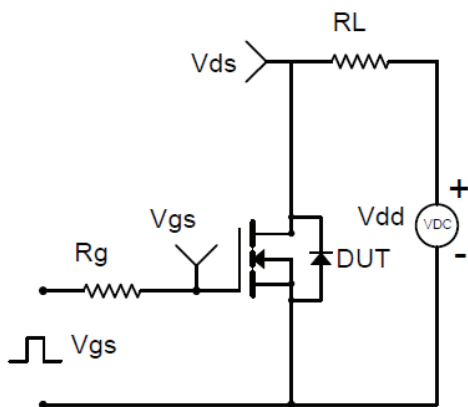


Fig.1-2 Switching Waveform

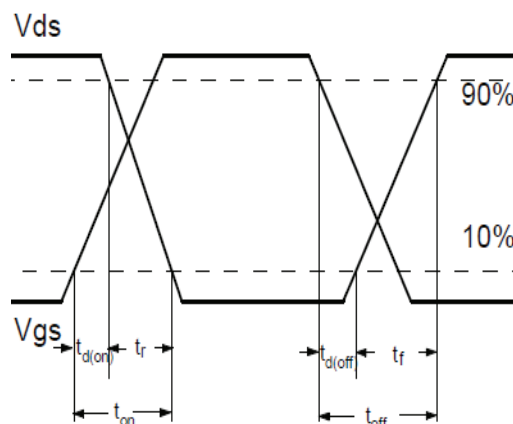


Fig.2-1 Gate charge test circuit

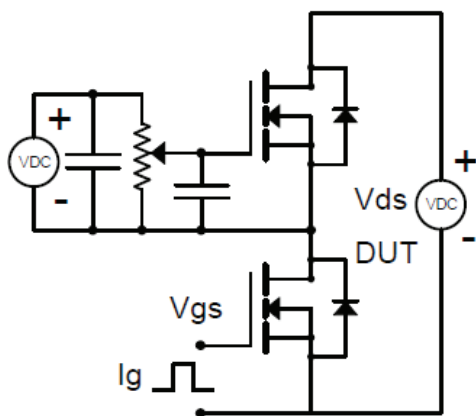


Fig.2-2 Gate charge waveform

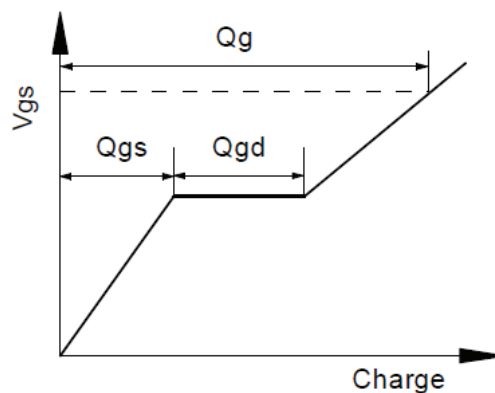


Fig.3-1 Avalanche test circuit

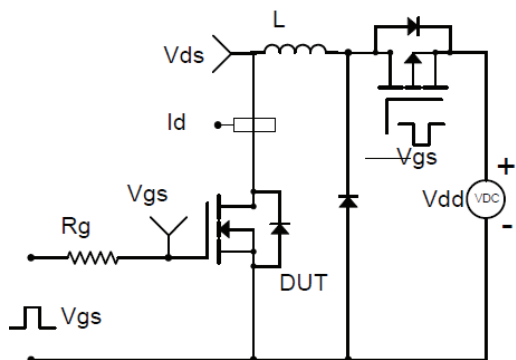
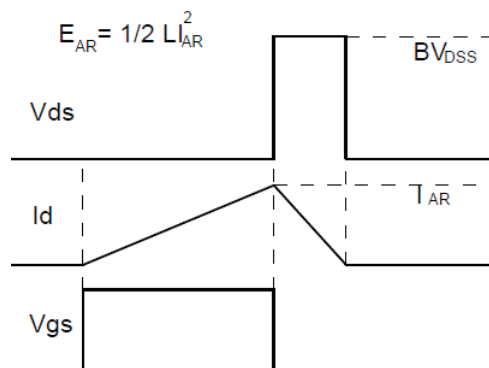
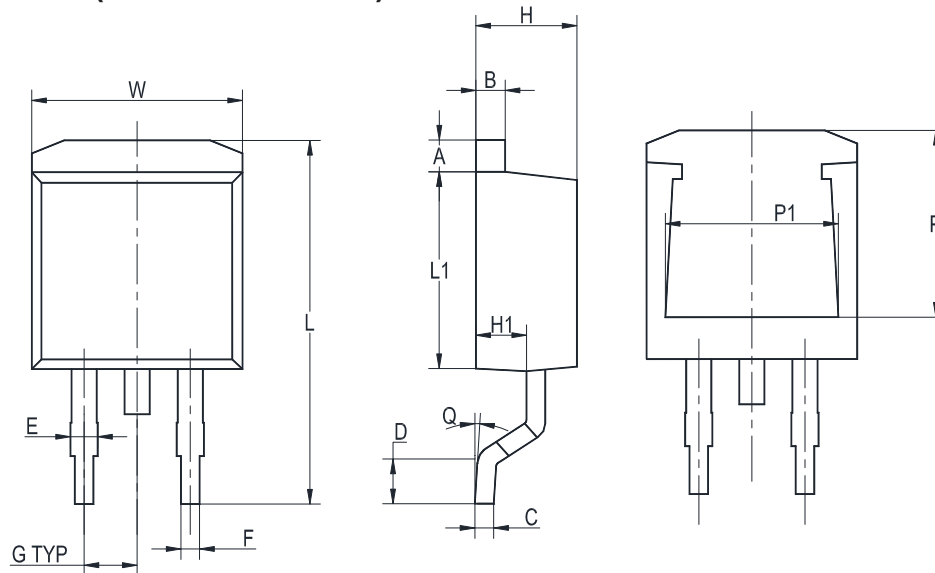


Fig.3-2 Avalanche waveform



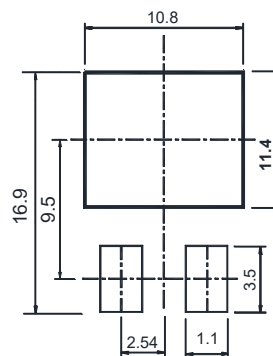
Package Outline (Dimensions in mm)

TO-263



UNIT	A	B	C	D	E	F	G	W	H	H1	L	L1	Q	P	P1
mm	1.5	1.5	0.5	2.60	1.6	0.94	2.54	10.5	4.8	2.9	16.5	8.7	8°	7.6	8.2
	1.1	1.1	0.3	2.15	1.1	0.68	TYP	9.6	4.4	2.5	14.5	8.2	MAX	7.1	7.4

Recommended Soldering Footprint



Packing information

Package	Reel Quantity	Box Quantity	Carton Quantity	Delivery Mode
TO-263	0.8 K / Reel	0.8 K / Box	4K pcs / Carton	Reel

Marking information

" TV04N040LS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



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